

3 VOLT 128K X 8 STATIC RAM**Features**

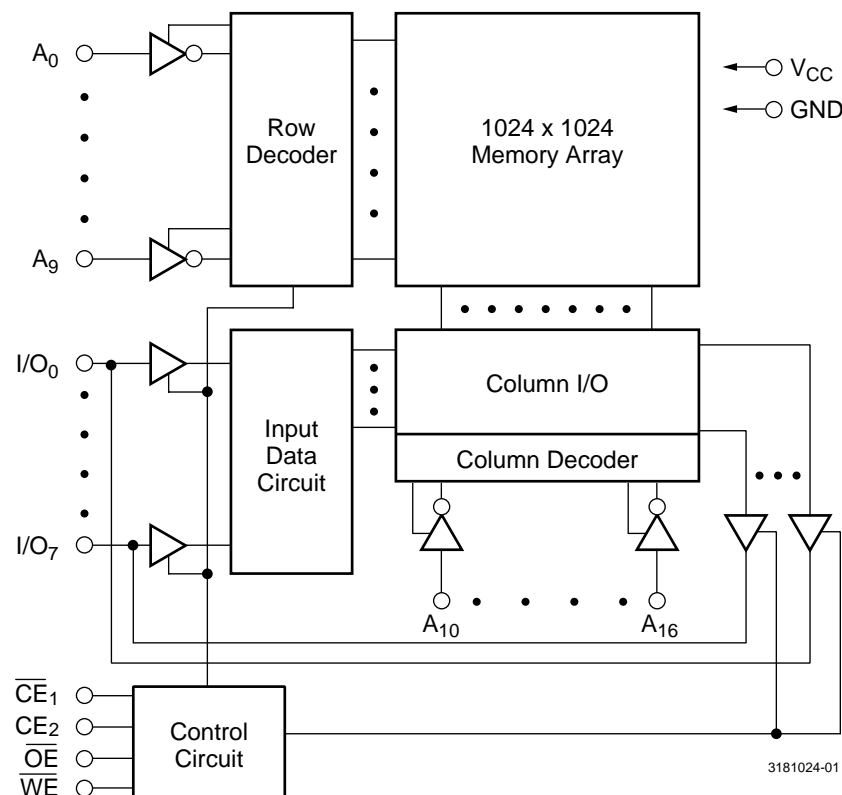
- High-speed: 45, 70 ns
- Ultra low DC operating current of 25 mA (max.)
 - TTL Standby: 1 mA (Max.)
 - CMOS Standby: 30 μ A (Max.)
- Fully static operation
- All inputs and outputs directly compatible
- Three state outputs
- Ultra low data retention current ($V_{CC} = 2V$)
- Extended operating voltage: 3.0V–3.6V

■ **Packages**

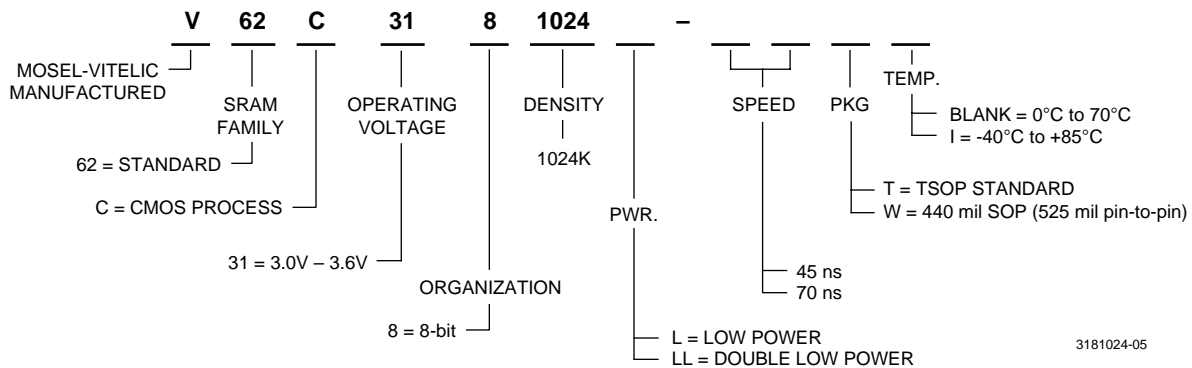
- 32-pin TSOP (Standard)
- 32-pin 440 mil SOP (525 mil pin-to-pin)

Description

The V62C3181024 is a 1,048,576-bit static random-access memory organized as 131,072 words by 8 bits. It is built with MOSEL VITELIC's high performance CMOS process. Inputs and three-state outputs are TTL compatible and allow for direct interfacing with common system bus structures.

Functional Block Diagram**Device Usage Chart**

Operating Temperature Range	Package Outline		Access Time (ns)		Power		Temperature Mark
	T	W	45	70	L	LL	
0°C to 70 °C	•	•	•	•	•	•	Blank
–40°C to +85°C	•	•	•			•	I

Part Number Information**Absolute Maximum Ratings ⁽¹⁾**

Symbol	Parameter	Commercial	Industrial	Units
V_{CC}	Supply Voltage	-0.5 to $V_{CC}+0.5$	-0.5 to $V_{CC}+0.5$	V
V_N	Input Voltage	-0.5 to +0.5	-0.5 to +0.5	V
V_{DQ}	Input/Output Voltage Applied	$V_{CC} + 0.3$	$V_{CC} + 0.3$	V
T_{BIAS}	Temperature Under Bias	-10 to +125	-65 to +135	°C
T_{STG}	Storage Temperature	-55 to +125	-65 to +150	°C

NOTE:

- Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Capacitance*

$T_A = 25^\circ\text{C}$, $f = 1.0\text{MHz}$

Symbol	Parameter	Conditions	Max.	Unit
C_{IN}	Input Capacitance	$V_{IN} = 0\text{V}$	6	pF
C_{OUT}	Output Capacitance	$V_{IO} = 0\text{V}$	8	pF

NOTE:

- This parameter is guaranteed and not tested.

Truth Table

Mode	\overline{CE}_1	CE_2	\overline{OE}	\overline{WE}	I/O Operation
Standby	H	X	X	X	High Z
Standby	X	L	X	X	High Z
Output Disable	L	H	H	H	High Z
Read	L	H	L	H	D_{OUT}
Write	L	H	X	L	D_{IN}

NOTE:

X = Don't Care, L = LOW, H = HIGH

DC Electrical Characteristics (over all temperature ranges, $V_{CC} = 3.0V - 3.6V$)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{CC}	Power Supply Voltage		3.0		3.6	V
V_{IL}	Input LOW Voltage ^(1,2)		-0.3	—	0.8	V
V_{IH}	Input HIGH Voltage ⁽¹⁾		2.2	—	$V_{CC} + 0.3$	V
I_{IL}	Input Leakage Current	$V_{CC} = \text{Max}$, $V_{IN} = 0V$ to V_{CC}	-2	—	2	μA
I_{OL}	Output Leakage Current	$V_{CC} = \text{Max}$, $\overline{CE}_1 = V_{IH}$, $V_{OUT} = 0V$ to V_{CC}	-2	—	2	μA
V_{OL}	Output LOW Voltage	$V_{CC} = \text{Min}$, $I_{OL} = 2.1mA$	—	—	0.4	V
V_{OH}	Output HIGH Voltage	$V_{CC} = \text{Min}$, $I_{OH} = -1mA$	2.4	—	—	V

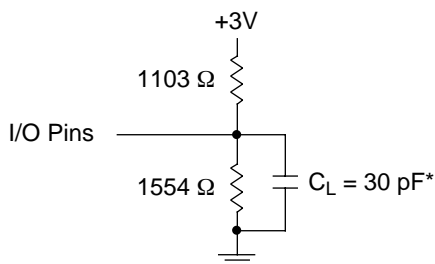
Symbol	Parameter		Power	Com. ⁽⁴⁾	Ind. ⁽⁴⁾	Units
I _{CC}	Operating Power Supply Current, $\overline{CE}_1 = V_{IL}$, $CE_2 = V_{IH}$, Output Open, $V_{CC} = \text{Max.}$, $f = 0$	READ	L	4	6	mA
			LL	3	5	
		WRITE	L	30	35	
			LL	25	30	
I _{CC1}	Average Operating Current, $\overline{CE}_1 = V_{IL}$, $CE_2 = V_{IH}$, Output Open, $V_{CC} = \text{Max.}$, $f = f_{\text{MAX}}^{(3)}$			60	80	mA
I _{SB}	TTL Standby Current $\overline{CE}_1 \geq V_{IH}$, $CE_2 \leq V_{IL}$, $V_{CC} = \text{Max.}$		L	2	4	mA
			LL	1	3	
I _{SB1}	CMOS Standby Current, $\overline{CE}_1 \geq V_{CC} - 0.2V$, $CE_2 \leq 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$ or $V_{IN} \leq 0.2V$, $V_{CC} = \text{Max.}$		L	50	60	μA
			LL	30	50	

NOTES:

- These are absolute values with respect to device ground and all overshoots due to system or tester noise are included.
- V_{IL} (Min.) = -3.0V for pulse width < 20ns.
- $f_{MAX} = 1/t_{RC}$.
- Maximum values.

AC Test Conditions

Input Pulse Levels	0 to 3V
Input Rise and Fall Times	5 ns
Timing Reference Levels	1.5V
Output Load	see below

AC Test Loads and Waveforms

* Includes scope and jig capacitance

Key to Switching Waveforms

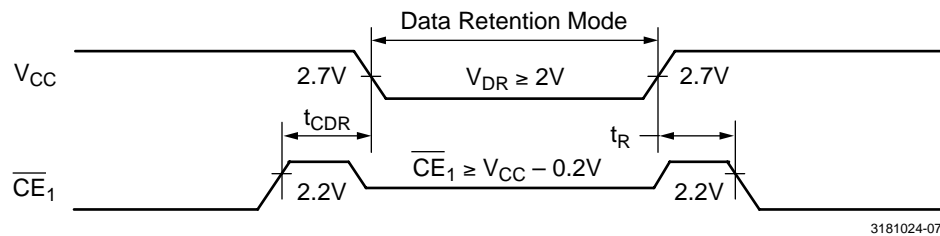
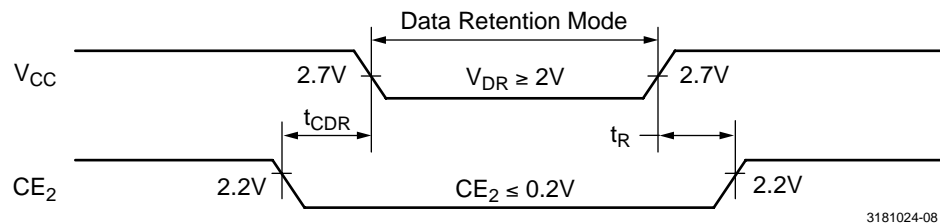
WAVEFORM	INPUTS	OUTPUTS
	MUST BE STEADY	WILL BE STEADY
	MAY CHANGE FROM H TO L	WILL BE CHANGING FROM H TO L
	MAY CHANGE FROM L TO H	WILL BE CHANGING FROM L TO H
	DON'T CARE: ANY CHANGE PERMITTED	CHANGING: STATE UNKNOWN
	DOES NOT APPLY	CENTER LINE IS HIGH IMPEDANCE "OFF" STATE

Data Retention Characteristics

Symbol	Parameter	Power	Min.	Typ. ⁽²⁾	Max.	Units
V_{DR}	V_{CC} for Data Retention $\overline{CE}_1 \geq V_{CC} - 0.2V$, $CE_2 \leq 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$, or $V_{IN} \leq 0.2V$		2.0	—	3.6	V
I_{CCDR}	Data Retention Current $\overline{CE}_1 \geq V_{DR} - 0.2V$, $CE_2 \leq 0.2V$, $V_{IN} \geq V_{CC} - 0.2V$, or $V_{IN} \leq 0.2V$	Com'l	L	—	2	μA
			LL	—	1	
		Ind.	L	—	—	
			LL	—	—	
t_{CDR}	Chip Deselect to Data Retention Time		0	—	—	ns
t_R	Operation Recovery Time (see Retention Waveform)		$t_{RC}^{(1)}$	—	—	ns

NOTES:

- t_{RC} = Read Cycle Time
- $T_A = +25^\circ C$.

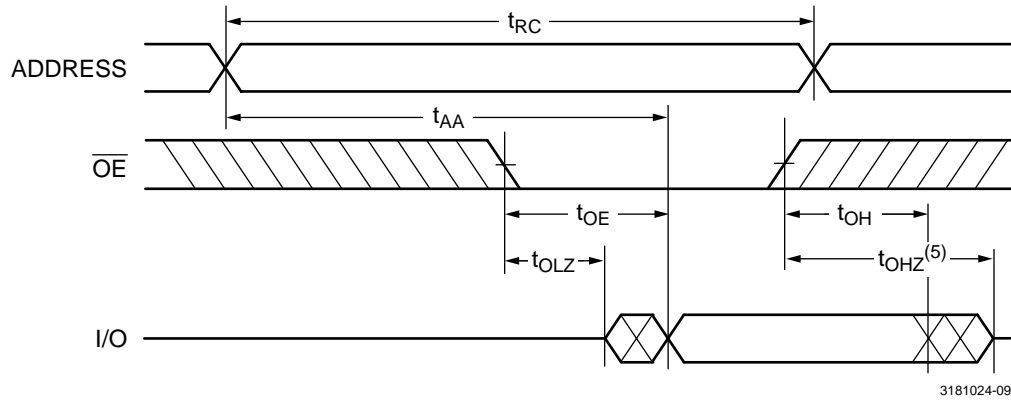
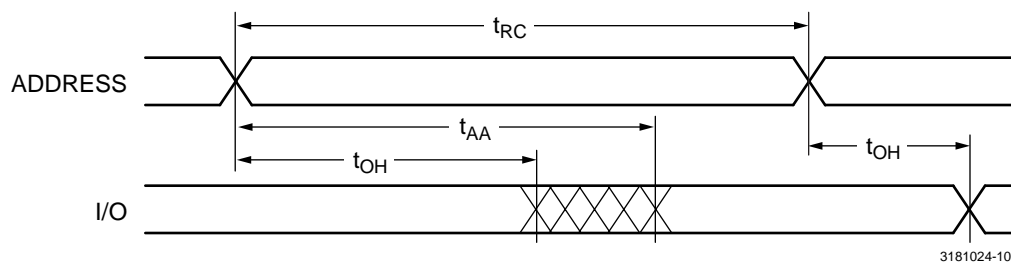
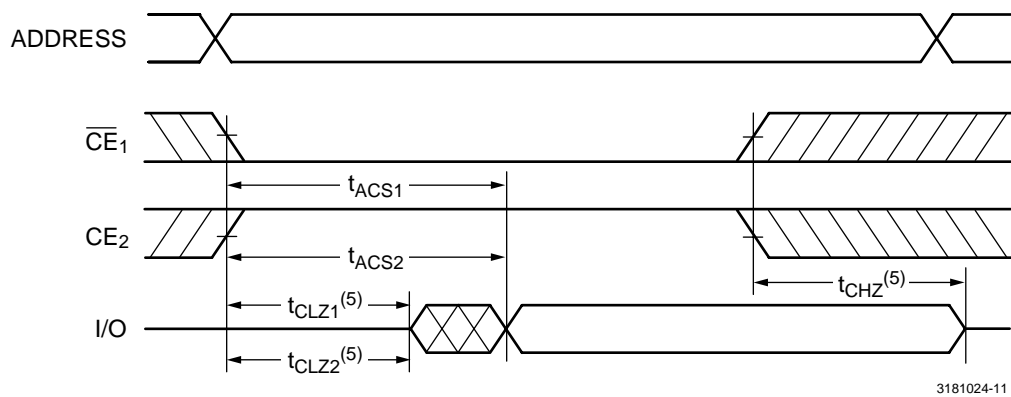
Low V_{CC} Data Retention Waveform (1) (\overline{CE}_1 Controlled)**Low V_{CC} Data Retention Waveform (2) (CE_2 Controlled)**

AC Electrical Characteristics(over all temperature ranges, $V_{CC} = 3.0V - 3.6V$)**Read Cycle**

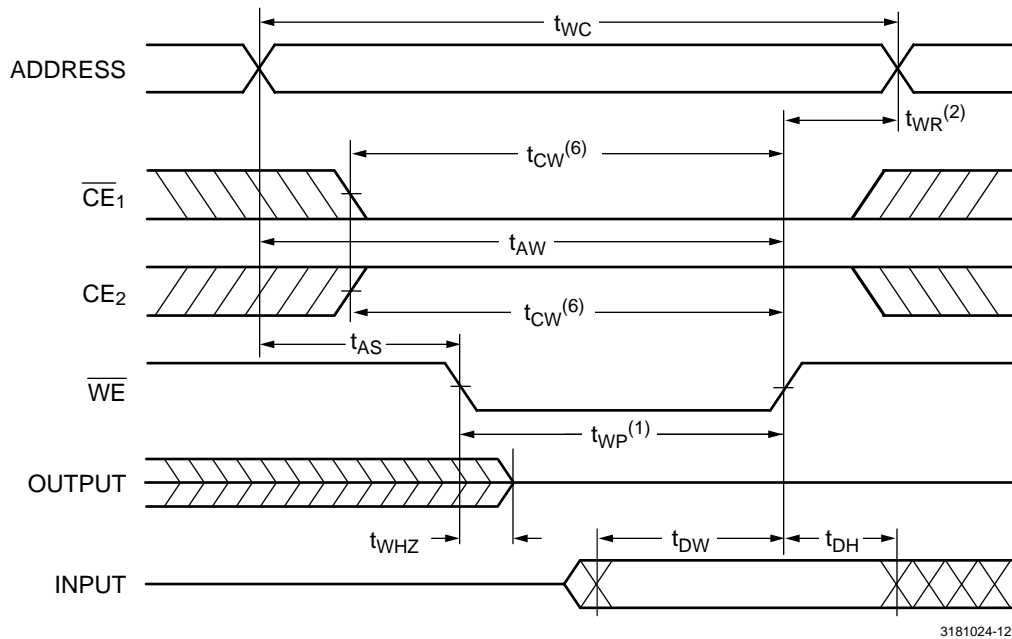
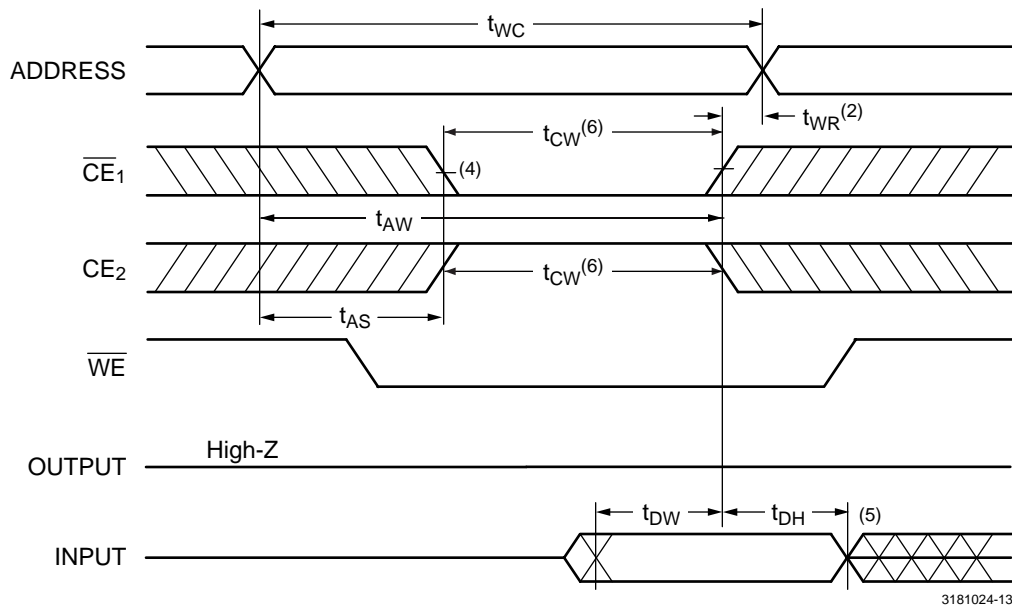
Parameter Name	Parameter	-45		-70		Unit
		Min.	Max.	Min.	Max.	
t_{RC}	Read Cycle Time	45	—	70	—	ns
t_{AA}	Address Access Time	—	45	—	70	ns
t_{ACS1}	Chip Enable Access Time	—	45	—	70	ns
t_{ACS2}	Chip Enable Access Time	—	45	—	70	ns
t_{OE}	Output Enable to Output Valid	—	15	—	35	ns
t_{CLZ1}	Chip Enable to Output in Low Z	5	—	10	—	ns
t_{CLZ2}	Chip Enable to Output in Low Z	5	—	10	—	ns
t_{OLZ}	Output Enable to Output in Low Z	5	—	5	—	ns
t_{CHZ}	Chip Disable to Output in High Z	0	15	0	25	ns
t_{OHZ}	Output Disable to Output in High Z	0	15	0	25	ns
t_{OH}	Output Hold from Address Change	3	—	3	—	ns
t_{PU}	Chip Enable to Power Up Time	0	—	0	—	ns
t_{PD}	Chip Enable to Power Down Time	—	45	—	70	ns

Write Cycle

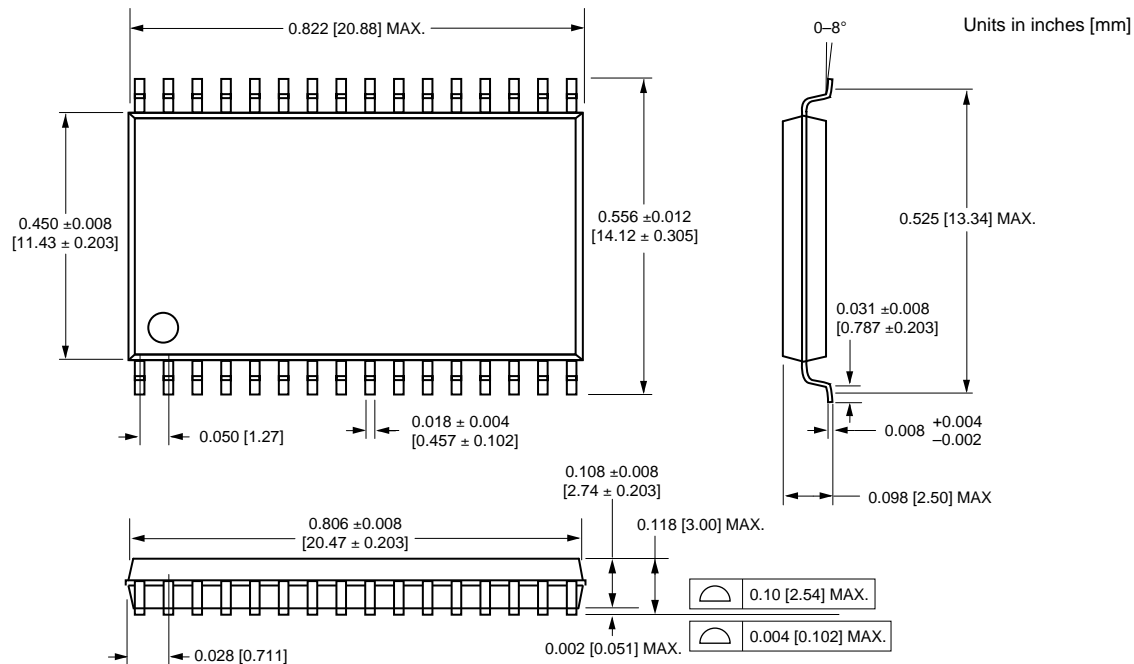
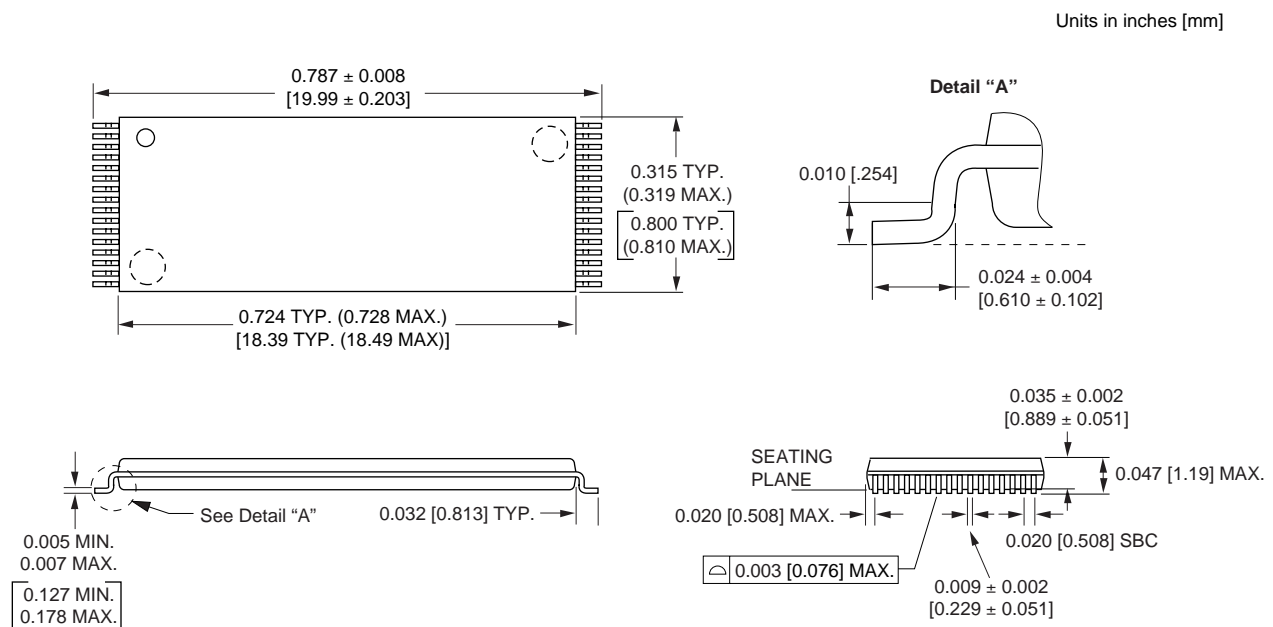
Parameter Name	Parameter	-45		-70		Unit
		Min.	Max.	Min.	Max.	
t_{WC}	Write Cycle Time	45	—	70	—	ns
t_{CW1}	Chip Enable to End of Write	35	—	60	—	ns
t_{CW2}	Chip Enable to End of Write	35	—	60	—	ns
t_{AS}	Address Setup Time	0	—	0	—	ns
t_{AW}	Address Valid to End of Write	35	—	60	—	ns
t_{WP}	Write Pulse Width	35	—	50	—	ns
t_{WR}	Write Recovery Time	0	—	0	—	ns
t_{WHZ}	Write to Output High-Z	0	15	0	25	ns
t_{WLZ}	Write to Output Low Z	3	—	5	—	ns
t_{DW}	Data Setup to End of Write	20	—	30	—	ns
t_{DH}	Data Hold from End of Write	0	—	0	—	ns

Switching Waveforms (Read Cycle)**Read Cycle 1^(1, 2)****Read Cycle 2^(1, 2, 4)****Read Cycle 3^(1, 3, 4)****NOTES:**

1. $\overline{WE} = V_{IH}$.
2. $\overline{CE}_1 = V_{IL}$ and $CE_2 = V_{IH}$.
3. Address valid prior to or coincident with \overline{CE}_1 transition LOW and/or CE_2 transition HIGH.
4. $\overline{OE} = V_{IL}$.
5. Transition is measured $\pm 500\text{mV}$ from steady state with $C_L = 5\text{pF}$. This parameter is guaranteed and not 100% tested.

Switching Waveforms (Write Cycle)**Write Cycle 1 (\overline{WE} Controlled)⁽⁴⁾****Write Cycle 2 (\overline{CE} Controlled)⁽⁴⁾****NOTES:**

1. The internal write time of the memory is defined by the overlap of \overline{CE}_1 and CE_2 active and \overline{WE} low. All signals must be active to initiate and any one signal can terminate a write by going inactive. The data input setup and hold timing should be referenced to the second transition edge of the signal that terminates the write.
2. t_{WR} is measured from the earlier of \overline{CE}_1 or \overline{WE} going high, or CE_2 going LOW at the end of the write cycle.
3. During this period, I/O pins are in the output state so that the input signals of opposite phase to the outputs must not be applied.
4. $\overline{OE} = V_{IL}$ or V_{IH} . However it is recommended to keep \overline{OE} at V_{IH} during write cycle to avoid bus contention.
5. If \overline{CE}_1 is LOW and CE_2 is HIGH during this period, I/O pins are in the output state. Then the data input signals of opposite phase to the outputs must not be applied to them.
6. t_{CW} is measured from \overline{CE}_1 going low or CE_2 going HIGH to the end of write.

Package Diagrams**32-Pin 440 mil SOP (525 mil pin-to-pin)****32-Pin TSOP (Standard)**

Notes

Notes

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